

MMBT4403

Rev.G May.-2023

描述 / Descriptions

SOT-23 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

特征 / Features

集电极电流可达 500mA。

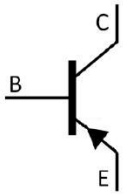
Collector currents up to 500 mA.

用途 / Applications

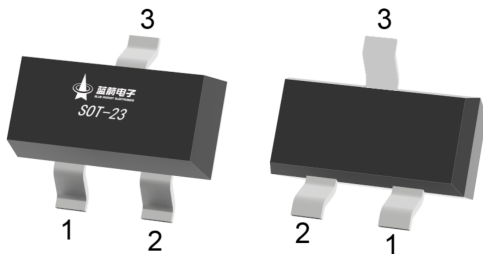
用于普通放大及开关电路。

General purpose amplifier and switch requiring.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN 1 : Base

PIN 2 : Emitter

PIN 3 : Collector

放大及印章代码 / hFE Classifications & Marking

hFE Range	100~300
Marking	2TH

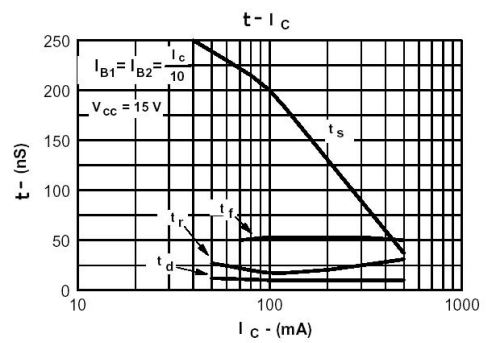
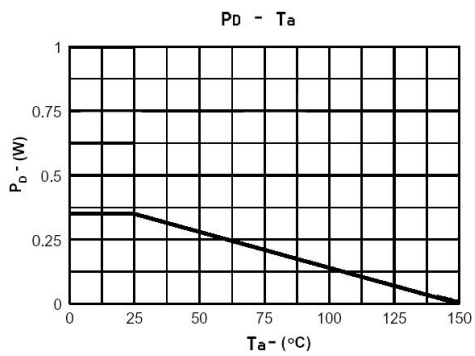
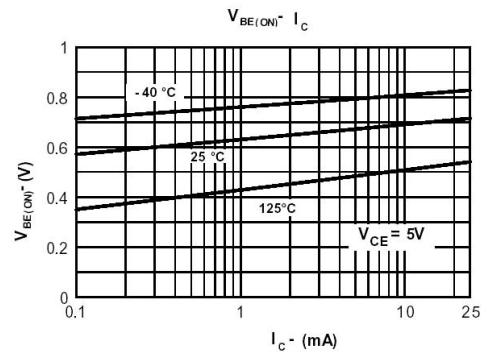
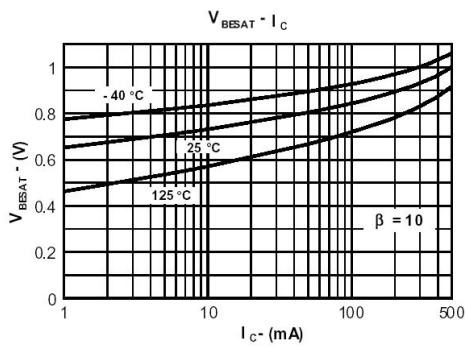
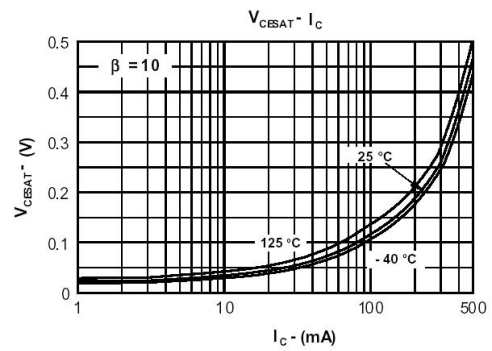
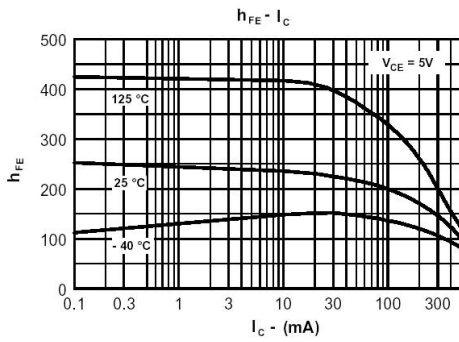
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V _{CB0}	-40	V
Collector to Emitter Voltage	V _{CE0}	-40	V
Emitter to Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-600	mA
Collector Power Dissipation	P _C	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V _{CB0}	I _C =-0.1mA I _E =0	-40			V
Collector to Emitter Breakdown Voltage	V _{CE0}	I _C =-1.0mA I _B =0	-40			V
Emitter to Base Breakdown Voltage	V _{EBO}	I _E =-0.1mA I _C =0	-5.0			V
Collector Cut-Off Current	I _{CB0}	V _{CB} =-40V I _E =0			-50	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5.0V I _C =0			-50	nA
DC Current Gain	h _{FE(1)}	V _{CE} =-2.0V I _C =-150mA	100		300	
	h _{FE(2)}	V _{CE} =-1.0V I _C =-0.1mA	30			
	h _{FE(3)}	V _{CE} =-1.0V I _C =-1.0mA	60			
	h _{FE(4)}	V _{CE} =-1.0V I _C =-10mA	100			
	h _{FE(5)}	V _{CE} =-2.0V I _C =-500mA	20			
Collector-Emitter Saturation voltage	V _{CE(sat) (1)}	I _C =-150mA I _B =-15mA			-0.4	V
	V _{CE(sat) (2)}	I _C =-500mA I _B =-50mA			-0.75	V
Base-Emitter Saturation Voltage	V _{BE(sat) (1)}	I _C =-150mA I _B =-15mA	-0.75		-0.95	V
	V _{BE(sat) (2)}	I _C =-500mA I _B =-50mA			-1.3	V
Transition Frequency	f _T	V _{CE} =-10V I _C =-20mA f=100MHz	200			MHz
Delay Time	t _d	V _{CC} =-30V I _C =-150mA I _{B1} =-15mA			15	ns
Rise Time	t _r				20	ns
Storage Time	t _s	V _{CC} =-30V I _C =-150mA I _{B1} =I _{B2} =-15mA			225	ns
Fall Time	t _f				30	ns

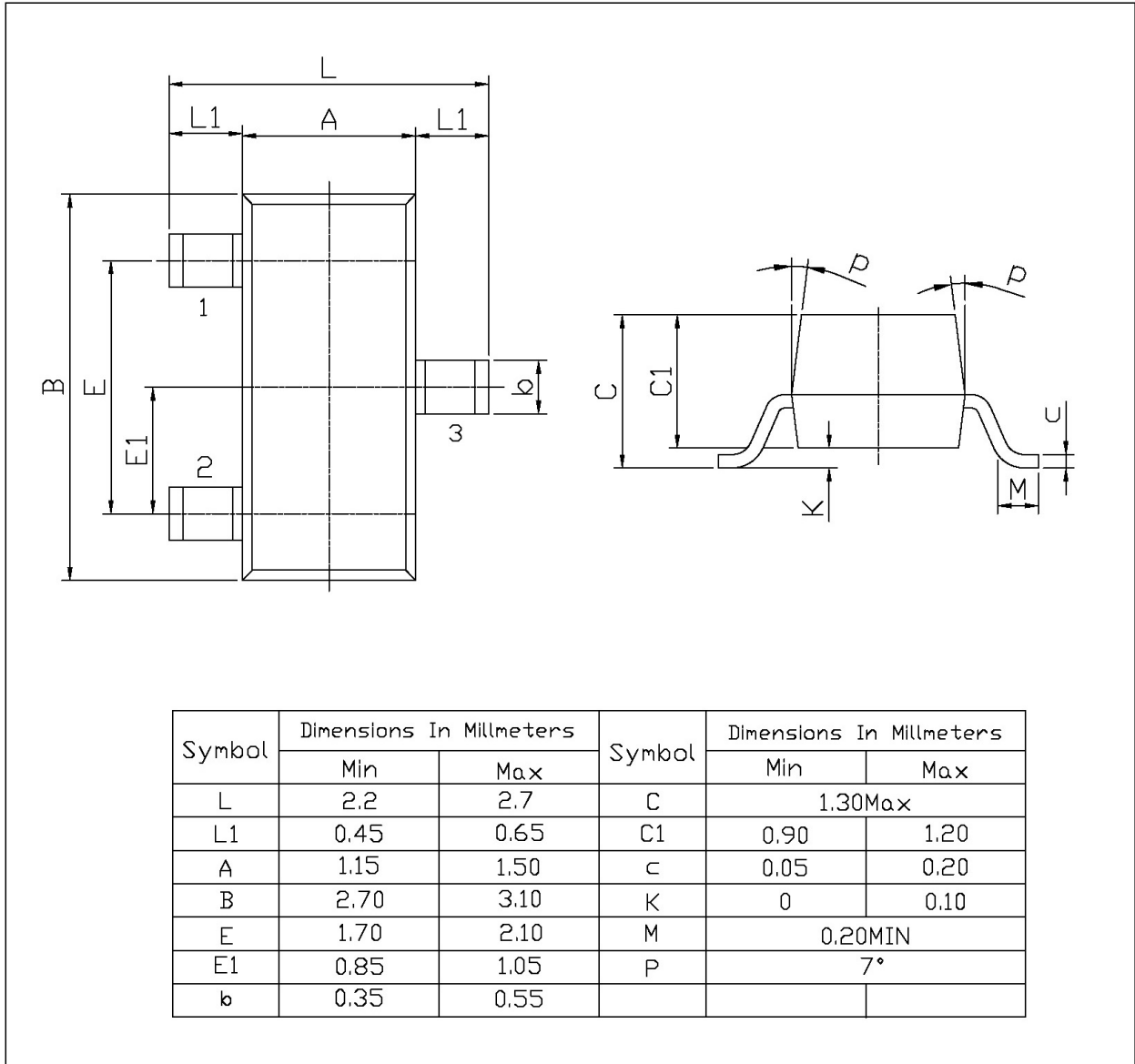
电参数曲线图 / Electrical Characteristic Curve



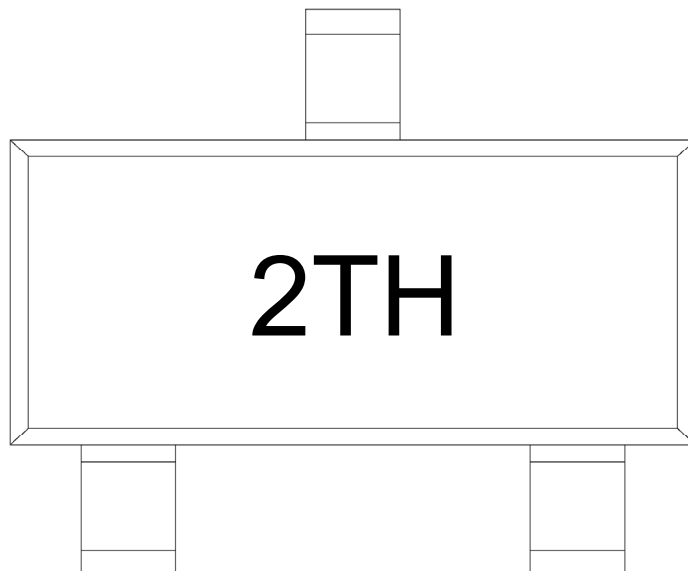
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



印章说明 / Marking Instructions



说明：

2T： 为型号代码

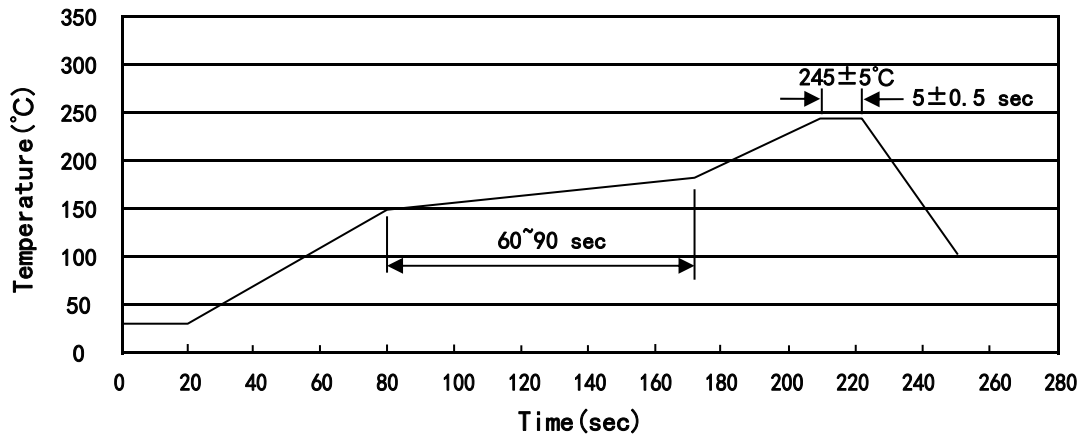
H： 为公司代码

Note:

2T： Product Type Code

H： Company Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices